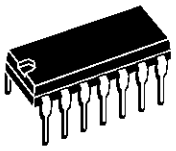
SGS-THOMSON MICROELECTRONICS

74AC125

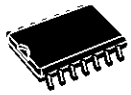
QUAD BUS BUFFERS (3-STATE)

PRELIMINARY DATA

- HIGH SPEED: t_{PD} = 5 ns (TYP.) at V_{CC} = 5V
- LOW POWER DISSIPATION: I_{CC} = 8 µA (MAX.) at T_A = 25 °C
- HIGH NOISE IMMUNITY: $V_{NIH} = V_{NIL}$ = 28% V_{CC} (MIN.)
- 50Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE: $|I_{OH}| = I_{OL}$ = 24 mA (MIN)
- BALANCED PROPAGATION DELAYS: $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 125
- IMPROVED LATCH-UP IMMUNITY



B
(Plastic Package)



M
(Micro Package)

ORDER CODES :

74AC125B 74AC125M

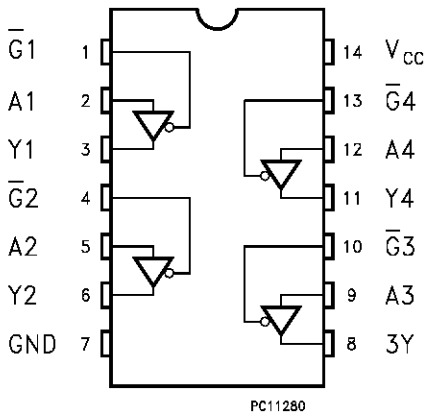
DESCRIPTION

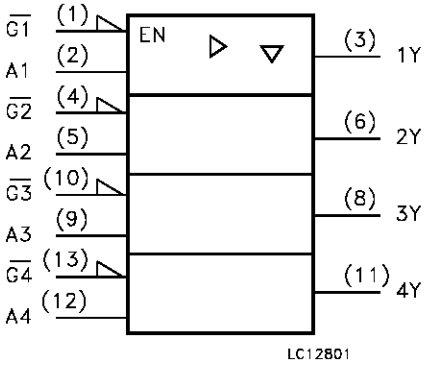
The AC125 is an high-speed CMOS QUAD BUS BUFFERS fabricated with sub-micron silicon gate and double-layer metal wiring C^2MOS technology. It is ideal for low power applications maintaining high speed operation similar to equivalent Bipolar Schottky TTL.

These devices require the same 3-STATE control input $\overline{G}$ to be taken high to make the output go in to the high impedance state.

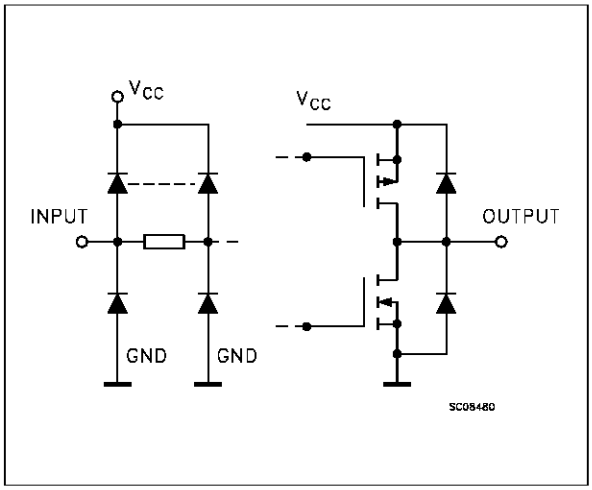
All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS





INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	$\overline{G1}$ to $\overline{G4}$	Output Enable Inputs
2, 5, 9, 12	A1 to A4	Data Inputs
3, 6, 8, 11	Y1 to Y4	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

TRUTH TABLE

A	$\overline{G}$	Y
X	H	Z
L	L	L
H	L	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 50	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 200	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2 to 6	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature:	-40 to +85	°C
dt/dv	Input Rise and Fall Time V_{CC} = 3.0, 4.5 or 5.5 V(note 1)	8	ns/V

1) V_{IN} from 30% to 70% of V_{CC}

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions			Value					Unit
		V_{CC} (V)			T_A = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	3.0	V_O = 0.1 V or V_{CC} - 0.1 V		2.1	1.5		2.1		V
		4.5			3.15	2.25		3.15		
		5.5			3.85	2.75		3.85		
V_{IL}	Low Level Input Voltage	3.0	V_O = 0.1 V or V_{CC} - 0.1 V			1.5	0.9		0.9	V
		4.5				2.25	1.35		1.35	
		5.5				2.75	1.65		1.65	
V_{OH}	High Level Output Voltage	3.0	V_I(*) = V_{IH} or V_{IL}	I_O=-50 µA	2.9	2.99		2.9		V
		4.5		I_O=-50 µA	4.4	4.49		4.4		
		5.5		I_O=-50 µA	5.4	5.49		5.4		
		3.0		I_O=-12 mA	2.56			2.46		
		4.5		I_O=-24 mA	3.86			3.76		
		5.5		I_O=-24 mA	4.86			4.76		
V_{OL}	Low Level Output Voltage	3.0	V_I(*) = V_{IH} or V_{IL}	I_O=50 µA		0.002	0.1		0.1	V
		4.5		I_O=50 µA		0.001	0.1		0.1	
		5.5		I_O=50 µA		0.001	0.1		0.1	
		3.0		I_O=12 mA			0.36		0.44	
		4.5		I_O=24 mA			0.36		0.44	
		5.5		I_O=24 mA			0.36		0.44	
I_I	Input Leakage Current	5.5	V_I = V_{CC} or GND				±0.1		±1	µA
I_{OZ}	3 State Output Leakage Current	5.5	V_I = V_{IH} or V_{IL} V_O = V_{CC} or GND				±0.5		±5	µA
I_{CC}	Quiescent Supply Current	5.5	V_I = V_{CC} or GND				8		80	µA
I_{OLD}	Dynamic Output Current (note 1, 2)	5.5	V_{OLD} = 1.65 V max						75	mA
I_{OHD}			V_{OHD} = 3.85 V min						-75	mA

1) Maximum test duration 2ms, one output loaded at time
2) Incident wave switching is guaranteed on transmission lines with impedances as low as 50 Ω.
(*) All outputs loaded.

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, R_L = 500 Ω, Input $t_r = t_f$ = 3 ns)

Symbol	Parameter	Test Condition		Value					Unit
		V_{CC} (V)		T_A = 25 °C			-40 to 85 °C		
				Min.	Typ.	Max.	Min.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	3.3(*)		1.0	6.5	9.0	1.0	10.0	ns
		5.0(**)		1.0	5.0	7.0	1.0	7.5	
t_{PZL} t_{PZH}	Output Enable Time	3.3(*)		1.0	6.0	10.0	1.0	11.0	ns
		5.0(**)		1.0	5.0	7.0	1.0	8.0	
t_{PLZ} t_{PHZ}	Output Disable Time	3.3(*)		1.0	7.5	10.0	1.0	11.0	ns
		5.0(**)		1.0	6.5	9.0	1.0	9.5	

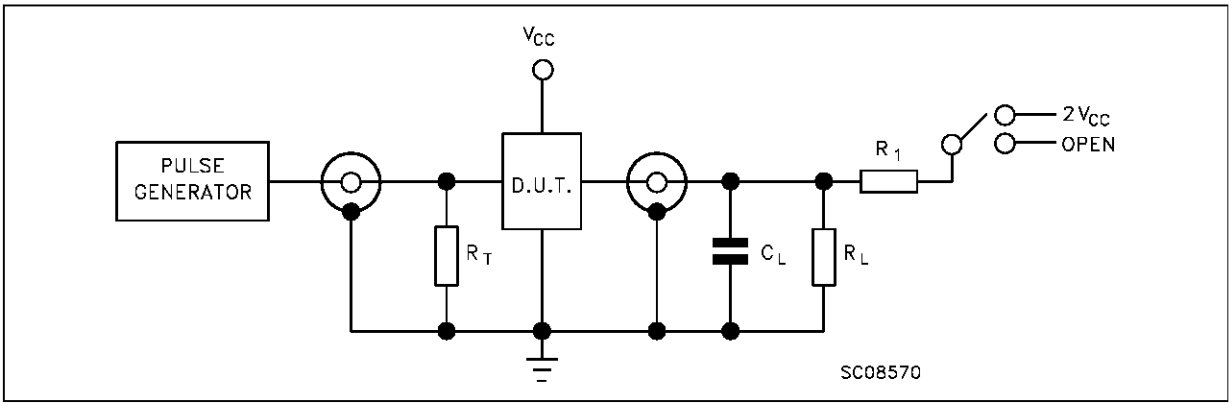
(*) Voltage range is 3.3V ± 0.3V
(**) Voltage range is 5V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value					Unit
		V_{CC} (V)		T_A = 25 °C			-40 to 85 °C		
				Min.	Typ.	Max.	Min.	Max.	
C_{IN}	Input Capacitance	5.0			4				pF
C_{OUT}	Output Capacitance	5.0			8				pF
C_{PD}	Power Dissipation Capacitance (note 1)	5.0			TBD				pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/n$ (per circuit)

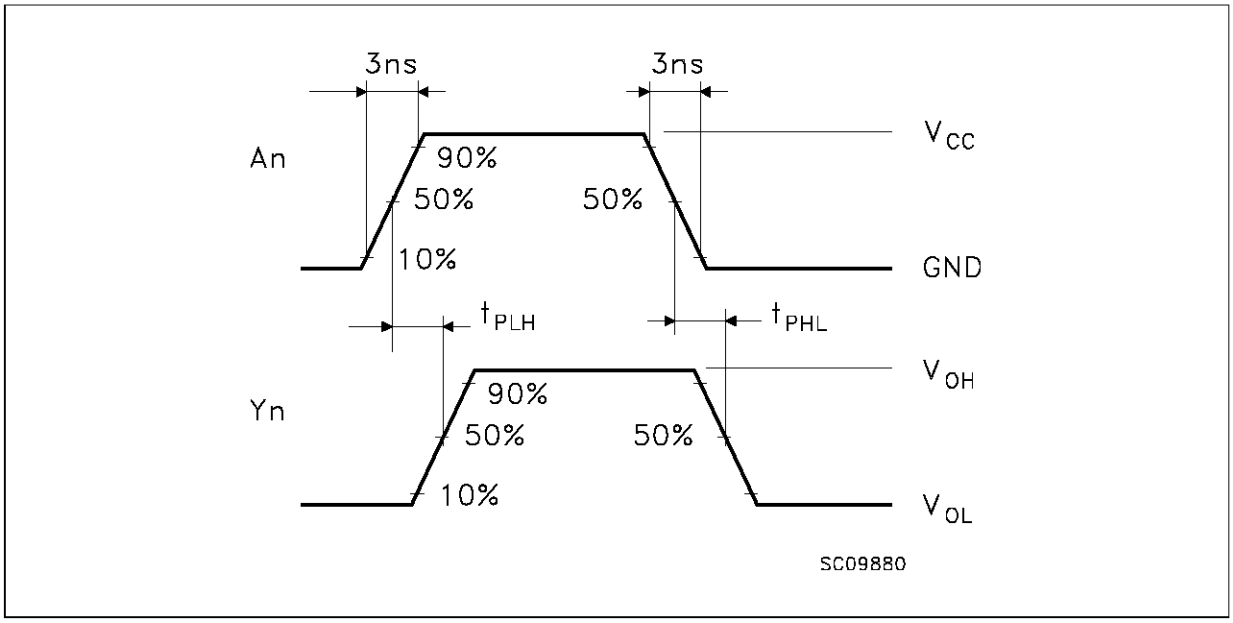
TEST CIRCUIT



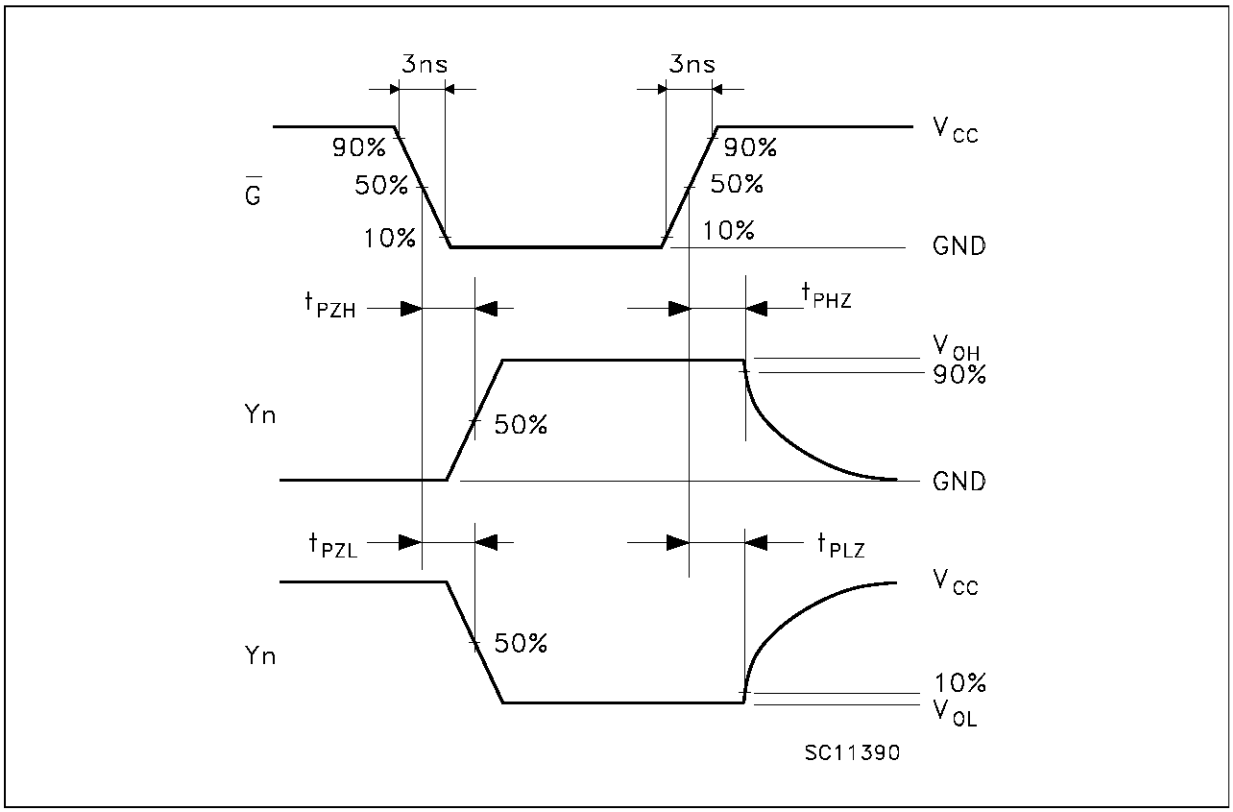
TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	$2V_{CC}$
t_{PZH}, t_{PHZ}	Open

C_L = 50 pF or equivalent (includes jig and probe capacitance)
$R_L = R_1$ = 500Ω or equivalent
$R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)

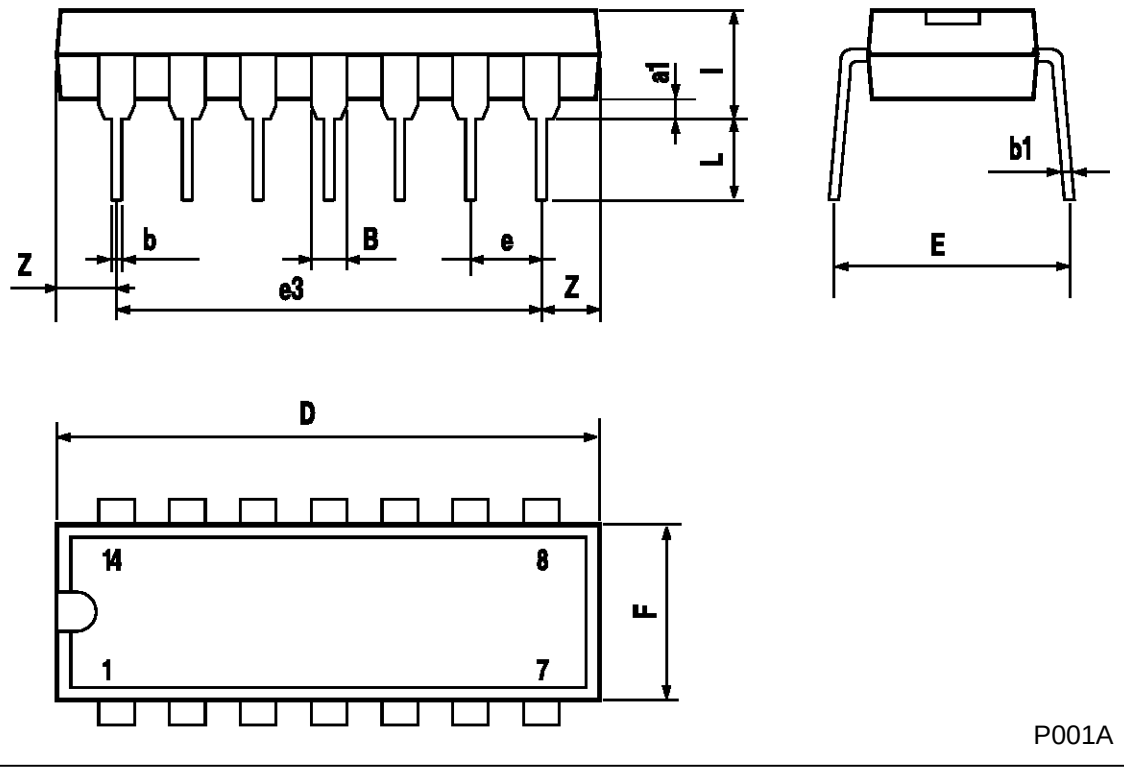


WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME (f=1MHz; 50% duty cycle)



Plastic DIP-14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



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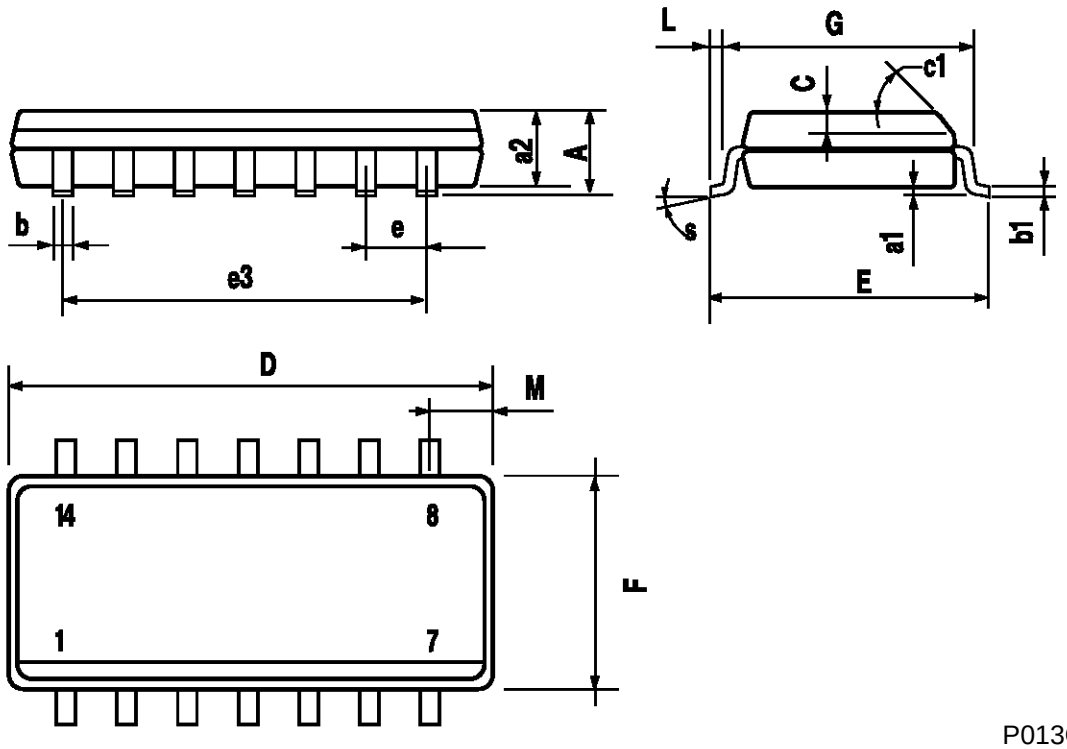
SO-14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45 (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8 (max.)					



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